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# Understanding <u>Embedded - FPGAs (Field Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	77
Number of Gates	30000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pn030-z2vq100i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Global Resources in Low Power Flash Devices

# **Global Resource Support in Flash-Based Devices**

The flash FPGAs listed in Table 3-1 support the global resources and the functions described in this document.

Table 3-1 • Flash-Based FPGAs

Series	Family*	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
	IGLOO nano	The industry's lowest-power, smallest-size solution
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM <sup>®</sup> Cortex <sup>™</sup> -M1 soft processors, and flash memory into a monolithic device

Note: \*The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

### IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO products as listed in Table 3-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

### **ProASIC3 Terminology**

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 3-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.



# Chip and Quadrant Global I/Os

The following sections give an overview of naming conventions and other related I/O information.

## Naming of Global I/Os

In low power flash devices, the global I/Os have access to certain clock conditioning circuitry and have direct access to the global network. Additionally, the global I/Os can be used as regular I/Os, since they have identical capabilities to those of regular I/Os. Due to the comprehensive and flexible nature of the I/Os in low power flash devices, a naming scheme is used to show the details of the I/O. The global I/O uses the generic name Gmn/IOuxwByVz. Note that Gmn refers to a global input pin and IOuxwByVz refers to a regular I/O Pin, as these I/Os can be used as either global or regular I/Os. Refer to the I/O Structures chapter of the user's guide for the device that you are using for more information on this naming convention.

Figure 3-4 represents the global input pins connection. It shows all 54 global pins available to access the 18 global networks in ProASIC3E families.

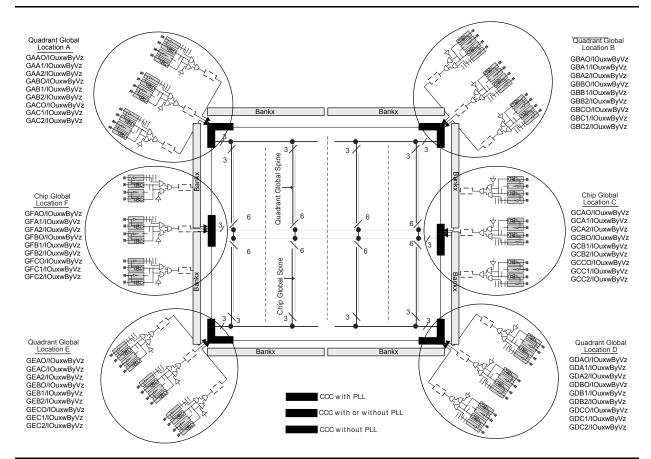


Figure 3-4 • Global Connections Details

# **Spine Architecture**

The low power flash device architecture allows the VersaNet global networks to be segmented. Each of these networks contains spines (the vertical branches of the global network tree) and ribs that can reach all the VersaTiles inside its region. The nine spines available in a vertical column reside in global networks with two separate regions of scope: the quadrant global network, which has three spines, and the chip (main) global network, which has six spines. Note that the number of quadrant globals and globals/spines per tree varies depending on the specific device. Refer to Table 3-4 for the clocking resources available for each device. The spines are the vertical branches of the global network tree, shown in Figure 3-3 on page 34. Each spine in a vertical column of a chip (main) global network is further divided into two spine segments of equal lengths: one in the top and one in the bottom half of the die (except in 10 k through 30 k gate devices).

Top and bottom spine segments radiating from the center of a device have the same height. However, just as in the ProASIC family, signals assigned only to the top and bottom spine cannot access the middle two rows of the die. The spines for quadrant clock networks do not cross the middle of the die and cannot access the middle two rows of the architecture.

Each spine and its associated ribs cover a certain area of the device (the "scope" of the spine; see Figure 3-3 on page 34). Each spine is accessed by the dedicated global network MUX tree architecture, which defines how a particular spine is driven—either by the signal on the global network from a CCC, for example, or by another net defined by the user. Details of the chip (main) global network spine-selection MUX are presented in Figure 3-8 on page 44. The spine drivers for each spine are located in the middle of the die.

Quadrant spines can be driven from user I/Os or an internal signal from the north and south sides of the die. The ability to drive spines in the quadrant global networks can have a significant effect on system performance for high-fanout inputs to a design. Access to the top quadrant spine regions is from the top of the die, and access to the bottom quadrant spine regions is from the bottom of the die. The A3PE3000 device has 28 clock trees and each tree has nine spines; this flexible global network architecture enables users to map up to 252 different internal/external clocks in an A3PE3000 device.

Table 3-4 • Globals/Spines/Rows for IGLOO and ProASIC3 Devices

ProASIC3/ ProASIC3L Devices	IGLOO Devices	Chip Globals	Quadrant Globals (4×3)	Clock Trees	Globals/ Spines per Tree	Total Spines per Device	VersaTiles in Each Tree	Total VersaTiles	Rows in Each Spine
A3PN010	AGLN010	4	0	1	0	0	260	260	4
A3PN015	AGLN015	4	0	1	0	0	384	384	6
A3PN020	AGLN020	4	0	1	0	0	520	520	6
A3PN060	AGLN060	6	12	4	9	36	384	1,536	12
A3PN125	AGLN125	6	12	8	9	72	384	3,072	12
A3PN250	AGLN250	6	12	8	9	72	768	6,144	24
A3P015	AGL015	6	0	1	9	9	384	384	12
A3P030	AGL030	6	0	2	9	18	384	768	12
A3P060	AGL060	6	12	4	9	36	384	1,536	12
A3P125	AGL125	6	12	8	9	72	384	3,072	12
A3P250/L	AGL250	6	12	8	9	72	768	6,144	24
A3P400	AGL400	6	12	12	9	108	768	9,216	24
A3P600/L	AGL600	6	12	12	9	108	1,152	13,824	36
A3P1000/L	AGL1000	6	12	16	9	144	1,536	24,576	48
A3PE600/L	AGLE600	6	12	12	9	108	1,120	13,440	35
A3PE1500		6	12	20	9	180	1,888	37,760	59
A3PE3000/L	AGLE3000	6	12	28	9	252	2,656	74,368	83



ProASIC3 nano FPGA Fabric User's Guide

You can control the maximum number of shared instances allowed for the legalization to take place using the Compile Option dialog box shown in Figure 3-17. Refer to Libero SoC / Designer online help for details on the Compile Option dialog box. A large number of shared instances most likely indicates a floorplanning problem that you should address.

Figure 3-17 • Shared Instances in the Compile Option Dialog Box

### **Designer Flow for Global Assignment**

To achieve the desired result, pay special attention to global management during synthesis and place-and-route. The current Synplify tool does not insert more than six global buffers in the netlist by default. Thus, the default flow will not assign any signal to the quadrant global network. However, you can use attributes in Synplify and increase the default global macro assignment in the netlist. Designer v6.2 supports automatic quadrant global assignment, which was not available in Designer v6.1. Layout will make the choice to assign the correct signals to global. However, you can also utilize PDC and perform manual global assignment to overwrite any automatic assignment. The following step-by-step suggestions guide you in the layout of your design and help you improve timing in Designer:

- 1. Run Compile and check the Compile report. The Compile report has global information in the "Device Utilization" section that describes the number of chip and quadrant signals in the design. A "Net Report" section describes chip global nets, quadrant global nets, local clock nets, a list of nets listed by fanout, and net candidates for local clock assignment. Review this information. Note that YB or YC are counted as global only when they are used in isolation; if you use YB only and not GLB, this net is not shown in the global/quadrant nets report. Instead, it appears in the Global Utilization report.
- 2. If some signals have a very high fanout and are candidates for global promotion, promote those signals to global using the compile options or PDC commands. Figure 3-18 on page 54 shows the Globals Management section of the compile options. Select **Promote regular nets whose fanout is greater than** and enter a reasonable value for fanouts.



# **CCC Support in Microsemi's Flash Devices**

The flash FPGAs listed in Table 4-1 support the CCC feature and the functions described in this document.

Table 4-1 • Flash-Based FPGAs

Series	Family*	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
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	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
	IGLOO nano	The industry's lowest-power, smallest-size solution
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM <sup>®</sup> Cortex <sup>™</sup> -M1 soft processors, and flash memory into a monolithic device

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Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

# **Global Buffers with No Programmable Delays**

Access to the global / quadrant global networks can be configured directly from the global I/O buffer, bypassing the CCC functional block (as indicated by the dotted lines in Figure 4-1 on page 61). Internal signals driven by the FPGA core can use the global / quadrant global networks by connecting via the routed clock input of the multiplexer tree.

There are many specific CLKBUF macros supporting the wide variety of single-ended I/O inputs (CLKBUF) and differential I/O standards (CLKBUF\_LVDS/LVPECL) in the low power flash families. They are used when connecting global I/Os directly to the global/quadrant networks.

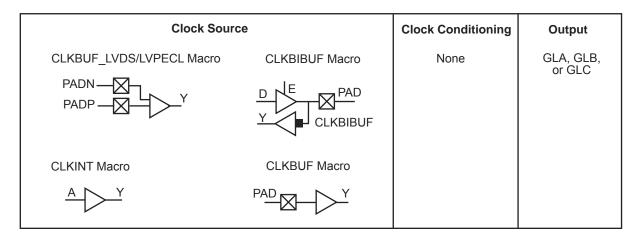
Note: IGLOO nano and ProASIC nano devices do not support differential inputs.

When an internal signal needs to be connected to the global/quadrant network, the CLKINT macro is used to connect the signal to the routed clock input of the network's MUX tree.

To utilize direct connection from global I/Os or from internal signals to the global/quadrant networks, CLKBUF, CLKBUF LVPECL/LVDS, and CLKINT macros are used (Figure 4-2).

- The CLKBUF and CLKBUF\_LVPECL/LVDS<sup>1</sup> macros are composite macros that include an I/O macro driving a global buffer, which uses a hardwired connection.
- The CLKBUF, CLKBUF\_LVPECL/LVDS<sup>1</sup> and CLKINT macros are pass-through clock sources and do not use the PLL or provide any programmable delay functionality.
- The CLKINT macro provides a global buffer function driven internally by the FPGA core.

The available CLKBUF macros are described in the *IGLOO*, *ProASIC3*, *SmartFusion*, and *Fusion Macro Library Guide*.



Note: IGLOO nano and ProASIC nano devices do not support differential inputs.

Figure 4-2 • CCC Options: Global Buffers with No Programmable Delay

# **Global Buffer with Programmable Delay**

Clocks requiring clock adjustments can utilize the programmable delay cores before connecting to the global / quadrant global networks. A maximum of 18 CCC global buffers can be instantiated in a device—three per CCC and up to six CCCs per device.

Each CCC functional block contains a programmable delay element for each of the global networks (up to three), and users can utilize these features by using the corresponding macro (Figure 4-3 on page 65).

<sup>1.</sup> B-LVDS and M-LVDS are supported with the LVDS macro.



Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

Each group of control bits is assigned a specific location in the configuration shift register. For a list of the 81 configuration bits (C[80:0]) in the CCC and a description of each, refer to "PLL Configuration Bits Description" on page 90. The configuration register can be serially loaded with the new configuration data and programmed into the CCC using the following ports:

- SDIN: The configuration bits are serially loaded into a shift register through this port. The LSB of the configuration data bits should be loaded first.
- SDOUT: The shift register contents can be shifted out (LSB first) through this port using the shift operation.
- SCLK: This port should be driven by the shift clock.
- SSHIFT: The active-high shift enable signal should drive this port. The configuration data will be shifted into the shift register if this signal is HIGH. Once SSHIFT goes LOW, the data shifting will be halted.
- SUPDATE: The SUPDATE signal is used to configure the CCC with the new configuration bits when shifting is complete.

To access the configuration ports of the shift register (SDIN, SDOUT, SSHIFT, etc.), the user should instantiate the CCC macro in his design with appropriate ports. Microsemi recommends that users choose SmartGen to generate the CCC macros with the required ports for dynamic reconfiguration.

Users must familiarize themselves with the architecture of the CCC core and its input, output, and configuration ports to implement the desired delay and output frequency in the CCC structure. Figure 4-22 shows a model of the CCC with configurable blocks and switches.



Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

### Loading the Configuration Register

The most important part of CCC dynamic configuration is to load the shift register properly with the configuration bits. There are different ways to access and load the configuration shift register:

- JTAG interface
- Logic core
- · Specific I/O tiles

#### JTAG Interface

The JTAG interface requires no additional I/O pins. The JTAG TAP controller is used to control the loading of the CCC configuration shift register.

Low power flash devices provide a user interface macro between the JTAG pins and the device core logic. This macro is called UJTAG. A user should instantiate the UJTAG macro in his design to access the configuration register ports via the JTAG pins.

For more information on CCC dynamic reconfiguration using UJTAG, refer to the "UJTAG Applications in Microsemi's Low Power Flash Devices" section on page 297.

#### **Logic Core**

If the logic core is employed, the user must design a module to provide the configuration data and control the shifting and updating of the CCC configuration shift register. In effect, this is a user-designed TAP controller, which requires additional chip resources.

#### Specific I/O Tiles

If specific I/O tiles are used for configuration, the user must provide the external equivalent of a TAP controller. This does not require additional core resources but does use pins.

### Shifting the Configuration Data

To enter a new configuration, all 81 bits must shift in via SDIN. After all bits are shifted, SSHIFT must go LOW and SUPDATE HIGH to enable the new configuration. For simulation purposes, bits <71:73> and <77:80> are "don't care."

The SUPDATE signal must be LOW during any clock cycle where SSHIFT is active. After SUPDATE is asserted, it must go back to the LOW state until a new update is required.

## **PLL Configuration Bits Description**

Table 4-8 • Configuration Bit Descriptions for the CCC Blocks

Config. Bits	Signal	Name	Description
<88:87>	GLMUXCFG [1:0] <sup>1</sup>	NGMUX configuration	The configuration bits specify the input clocks to the NGMUX (refer to Table 4-17 on page 94). <sup>2</sup>
86	OCDIVHALF <sup>1</sup>		When the PLL is bypassed, the 100 MHz RC oscillator can be divided by the divider factor in Table 4-18 on page 95.
85	OBDIVHALF <sup>1</sup>		When the PLL is bypassed, the 100 MHz RC oscillator can be divided by a 0.5 factor (refer to Table 4-18 on page 95).
84	OADIVHALF <sup>1</sup>		When the PLL is bypassed, the 100 MHz RC oscillator can be divided by certain 0.5 factor (refer to Table 4-16 on page 94).

#### Notes:

- 1. The <88:81> configuration bits are only for the Fusion dynamic CCC.
- This value depends on the input clock source, so Layout must complete before these bits can be set.
   After completing Layout in Designer, generate the "CCC\_Configuration" report by choosing Tools > Report > CCC\_Configuration. The report contains the appropriate settings for these bits.



# **Conclusion**

The advanced CCCs of the IGLOO and ProASIC3 devices are ideal for applications requiring precise clock management. They integrate easily with the internal low-skew clock networks and provide flexible frequency synthesis, clock deskewing, and/or time-shifting operations.

## **Related Documents**

## **Application Notes**

Board-Level Considerations
http://www.microsemi.com/soc/documents/ALL AC276 AN.pdf

### **Datasheets**

Fusion Family of Mixed Signal FPGAs http://www.microsemi.com/soc/documents/Fusion DS.pdf

### **User's Guides**

IGLOO, ProASIC3, SmartFusion, and Fusion Macro Library Guide http://www.microsemi.com/soc/documents/pa3 libguide ug.pdf

# **List of Changes**

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
August 2012	The "Implementing EXTFB in ProASIC3/E Devices" section is new (SAR 36647).	70
	Table 4-7 • Delay Values in Libero SoC Software per Device Family was added to the "Clock Delay Adjustment" section (SAR 22709).	86
	The "Phase Adjustment" section was rewritten to explain better why the visual CCC shows both the actual phase and the actual delay that is equivalent to this phase shift (SAR 29647).	87
	The hyperlink for the <i>Board-Level Considerations</i> application note was corrected (SAR 36663)	112, 113
December 2011	Figure 4-20 • PLL Block Diagram, Figure 4-22 • CCC Block Control Bits – Graphical Representation of Assignments, and Table 4-12 • MUXA, MUXB, MUXC were revised to change the phase shift assignments for PLLs 4 through 7 (SAR 33791).	85, 89, 93
June 2011	The description for RESETEN in Table 4-8 • Configuration Bit Descriptions for the CCC Blocks was revised. The phrase "and should not be modified via dynamic configuration" was deleted because RESETEN is read only (SAR 25949).	90
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
	Notes were added where appropriate to point out that IGLOO nano and ProASIC3 nano devices do not support differential inputs (SAR 21449).	N/A

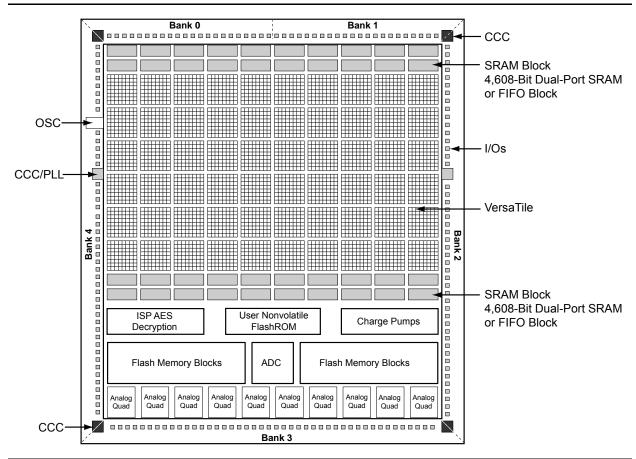


Figure 5-2 • Fusion Device Architecture Overview (AFS600)

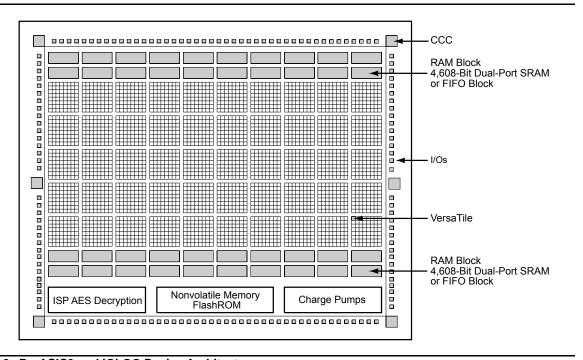


Figure 5-3 • ProASIC3 and IGLOO Device Architecture

# FlashROM Security

Low power flash devices have an on-chip Advanced Encryption Standard (AES) decryption core, combined with an enhanced version of the Microsemi flash-based lock technology (FlashLock®). Together, they provide unmatched levels of security in a programmable logic device. This security applies to both the FPGA core and FlashROM content. These devices use the 128-bit AES (Rijndael) algorithm to encrypt programming files for secure transmission to the on-chip AES decryption core. The same algorithm is then used to decrypt the programming file. This key size provides approximately  $3.4 \times 10^{38}$  possible 128-bit keys. A computing system that could find a DES key in a second would take approximately 149 trillion years to crack a 128-bit AES key. The 128-bit FlashLock feature in low power flash devices works via a FlashLock security Pass Key mechanism, where the user locks or unlocks the device with a user-defined key. Refer to the "Security in Low Power Flash Devices" section on page 235.

If the device is locked with certain security settings, functions such as device read, write, and erase are disabled. This unique feature helps to protect against invasive and noninvasive attacks. Without the correct Pass Key, access to the FPGA is denied. To gain access to the FPGA, the device first must be unlocked using the correct Pass Key. During programming of the FlashROM or the FPGA core, you can generate the security header programming file, which is used to program the AES key and/or FlashLock Pass Key. The security header programming file can also be generated independently of the FlashROM and FPGA core content. The FlashLock Pass Key is not stored in the FlashROM.

Low power flash devices with AES-based security allow for secure remote field updates over public networks such as the Internet, and ensure that valuable intellectual property (IP) remains out of the hands of IP thieves. Figure 5-5 shows this flow diagram.

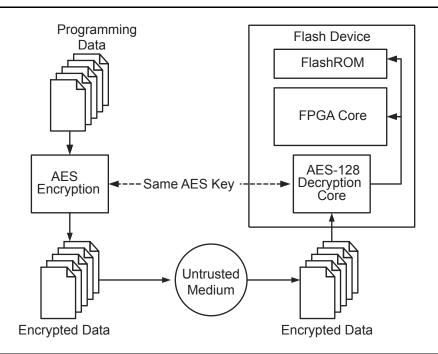


Figure 5-5 • Programming FlashROM Using AES

# **Programming and Accessing FlashROM**

The FlashROM content can only be programmed via JTAG, but it can be read back selectively through the JTAG programming interface, the UJTAG interface, or via direct FPGA core addressing. The pages of the FlashROM can be made secure to prevent read-back via JTAG. In that case, read-back on these secured pages is only possible by the FPGA core fabric or via UJTAG.

A 7-bit address from the FPGA core defines which of the eight pages (three MSBs) is being read, and which of the 16 bytes within the selected page (four LSBs) are being read. The FlashROM content can be read on a random basis; the access time is 10 ns for a device supporting commercial specifications. The FPGA core will be powered down during writing of the FlashROM content. FPGA power-down during FlashROM programming is managed on-chip, and FPGA core functionality is not available during programming of the FlashROM. Table 5-2 summarizes various FlashROM access scenarios.

Table 5-2 • FlashROM Read/Write	Capabilities	by	Access N	/lode
---------------------------------	--------------	----	----------	-------

Access Mode	FlashROM Read	FlashROM Write
JTAG	Yes	Yes
UJTAG	Yes	No
FPGA core	Yes	No

Figure 5-6 shows the accessing of the FlashROM using the UJTAG macro. This is similar to FPGA core access, where the 7-bit address defines which of the eight pages (three MSBs) is being read and which of the 16 bytes within the selected page (four LSBs) are being read. Refer to the "UJTAG Applications in Microsemi's Low Power Flash Devices" section on page 297 for details on using the UJTAG macro to read the FlashROM.

Figure 5-7 on page 123 and Figure 5-8 on page 123 show the FlashROM access from the JTAG port. The FlashROM content can be read on a random basis. The three-bit address defines which page is being read or updated.

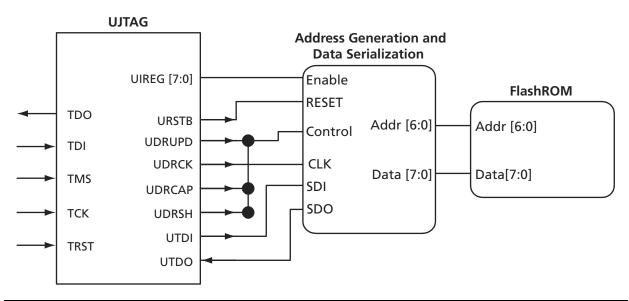


Figure 5-6 • Block Diagram of Using UJTAG to Read FlashROM Contents



SmartGen allows you to generate the FlashROM netlist in VHDL, Verilog, or EDIF format. After the FlashROM netlist is generated, the core can be instantiated in the main design like other SmartGen cores. Note that the macro library name for FlashROM is UFROM. The following is a sample FlashROM VHDL netlist that can be instantiated in the main design:

```
library ieee;
use ieee.std_logic_1164.all;
library fusion;
entity FROM_a is
  port( ADDR : in std_logic_vector(6 downto 0); DOUT : out std_logic_vector(7 downto 0));
end FROM a;
architecture DEF_ARCH of FROM_a is
  component UFROM
    generic (MEMORYFILE:string);
    port(D00, D01, D02, D03, D04, D05, D06, D07 : out std_logic;
      ADDRO, ADDR1, ADDR2, ADDR3, ADDR4, ADDR5, ADDR6 : in std_logic := 'U');
  end component;
  component GND
    port( Y : out std_logic);
  end component;
signal U_7_PIN2 : std_logic ;
begin
  GND_1_net : GND port map(Y => U_7_PIN2);
  UFROM0 : UFROM
  generic map(MEMORYFILE => "FROM_a.mem")
  port map(DO0 => DOUT(0), DO1 => DOUT(1), DO2 => DOUT(2), DO3 => DOUT(3), DO4 => DOUT(4),
    DO5 => DOUT(5), DO6 => DOUT(6), DO7 => DOUT(7), ADDR0 => ADDR(0), ADDR1 => ADDR(1),
    ADDR2 \Rightarrow ADDR(2), ADDR3 \Rightarrow ADDR(3), ADDR4 \Rightarrow ADDR(4), ADDR5 \Rightarrow ADDR(5),
    ADDR6 => ADDR(6));
end DEF_ARCH;
```

SmartGen generates the following files along with the netlist. These are located in the SmartGen folder for the Libero SoC project.

- 1. MEM (Memory Initialization) file
- 2. UFC (User Flash Configuration) file
- 3. Log file

The MEM file is used for simulation, as explained in the "Simulation of FlashROM Design" section on page 127. The UFC file, generated by SmartGen, has the FlashROM configuration for single or multiple devices and is used during STAPL generation. It contains the region properties and simulation values. Note that any changes in the MEM file will not be reflected in the UFC file. Do not modify the UFC to change FlashROM content. Instead, use the SmartGen GUI to modify the FlashROM content. See the "Programming File Generation for FlashROM Design" section on page 127 for a description of how the UFC file is used during the programming file generation. The log file has information regarding the file type and file location.

### **SRAM and FIFO Architecture**

To meet the needs of high-performance designs, the memory blocks operate strictly in synchronous mode for both read and write operations. The read and write clocks are completely independent, and each can operate at any desired frequency up to 250 MHz.

- 4k×1, 2k×2, 1k×4, 512×9 (dual-port RAM—2 read / 2 write or 1 read / 1 write)
- 512×9, 256×18 (2-port RAM—1 read / 1 write)
- Sync write, sync pipelined / nonpipelined read

Automotive ProASIC3 devices support single-port SRAM capabilities or dual-port SRAM only under specific conditions. Dual-port mode is supported if the clocks to the two SRAM ports are the same and 180° out of phase (i.e., the port A clock is the inverse of the port B clock). The Libero SoC software macro libraries support a dual-port macro only. For use of this macro as a single-port SRAM, the inputs and clock of one port should be tied off (grounded) to prevent errors during design compile. For use in dual-port mode, the same clock with an inversion between the two clock pins of the macro should be used in the design to prevent errors during compile.

The memory block includes dedicated FIFO control logic to generate internal addresses and external flag logic (FULL, EMPTY, AFULL, AEMPTY).

Simultaneous dual-port read/write and write/write operations at the same address are allowed when certain timing requirements are met.

During RAM operation, addresses are sourced by the user logic, and the FIFO controller is ignored. In FIFO mode, the internal addresses are generated by the FIFO controller and routed to the RAM array by internal MUXes.

The low power flash device architecture enables the read and write sizes of RAMs to be organized independently, allowing for bus conversion. For example, the write size can be set to 256×18 and the read size to 512×9.

Both the write width and read width for the RAM blocks can be specified independently with the WW (write width) and RW (read width) pins. The different D×W configurations are 256×18, 512×9, 1k×4, 2k×2, and 4k×1. When widths of one, two, or four are selected, the ninth bit is unused. For example, when writing nine-bit values and reading four-bit values, only the first four bits and the second four bits of each nine-bit value are addressable for read operations. The ninth bit is not accessible.

Conversely, when writing four-bit values and reading nine-bit values, the ninth bit of a read operation will be undefined. The RAM blocks employ little-endian byte order for read and write operations.

## **Memory Blocks and Macros**

Memory blocks can be configured with many different aspect ratios, but are generically supported in the macro libraries as one of two memory elements: RAM4K9 or RAM512X18. The RAM4K9 is configured as a true dual-port memory block, and the RAM512X18 is configured as a two-port memory block. Dual-port memory allows the RAM to both read from and write to either port independently. Two-port memory allows the RAM to read from one port and write to the other using a common clock or independent read and write clocks. If needed, the RAM4K9 blocks can be configured as two-port memory blocks. The memory block can be configured as a FIFO by combining the basic memory block with dedicated FIFO controller logic. The FIFO macro is named FIFO4KX18 (Figure 6-3 on page 136).

Clocks for the RAM blocks can be driven by the VersaNet (global resources) or by regular nets. When using local clock segments, the clock segment region that encompasses the RAM blocks can drive the RAMs. In the dual-port configuration (RAM4K9), each memory block port can be driven by either rising-edge or falling-edge clocks. Each port can be driven by clocks with different edges. Though only a rising-edge clock can drive the physical block itself, the Microsemi Designer software will automatically bubble-push the inversion to properly implement the falling-edge trigger for the RAM block.

#### **FIFO Flag Usage Considerations**

The AEVAL and AFVAL pins are used to specify the 12-bit AEMPTY and AFULL threshold values. The FIFO contains separate 12-bit write address (WADDR) and read address (RADDR) counters. WADDR is incremented every time a write operation is performed, and RADDR is incremented every time a read operation is performed. Whenever the difference between WADDR and RADDR is greater than or equal to AFVAL, the AFULL output is asserted. Likewise, whenever the difference between WADDR and RADDR is less than or equal to AEVAL, the AEMPTY output is asserted. To handle different read and write aspect ratios, AFVAL and AEVAL are expressed in terms of total data bits instead of total data words. When users specify AFVAL and AEVAL in terms of read or write words, the SmartGen tool translates them into bit addresses and configures these signals automatically. SmartGen configures the AFULL flag to assert when the write address exceeds the read address by at least a predefined value. In a 2k×8 FIFO, for example, a value of 1,500 for AFVAL means that the AFULL flag will be asserted after a write when the difference between the write address and the read address reaches 1,500 (there have been at least 1,500 more writes than reads). It will stay asserted until the difference between the write and read addresses drops below 1,500.

The AEMPTY flag is asserted when the difference between the write address and the read address is less than a predefined value. In the example above, a value of 200 for AEVAL means that the AEMPTY flag will be asserted when a read causes the difference between the write address and the read address to drop to 200. It will stay asserted until that difference rises above 200. Note that the FIFO can be configured with different read and write widths; in this case, the AFVAL setting is based on the number of write data entries, and the AEVAL setting is based on the number of read data entries. For aspect ratios of 512×9 and 256×18, only 4,096 bits can be addressed by the 12 bits of AFVAL and AEVAL. The number of words must be multiplied by 8 and 16 instead of 9 and 18. The SmartGen tool automatically uses the proper values. To avoid halfwords being written or read, which could happen if different read and write aspect ratios were specified, the FIFO will assert FULL or EMPTY as soon as at least one word cannot be written or read. For example, if a two-bit word is written and a four-bit word is being read, the FIFO will remain in the empty state when the first word is written. This occurs even if the FIFO is not completely empty, because in this case, a complete word cannot be read. The same is applicable in the full state. If a four-bit word is written and a two-bit word is read, the FIFO is full and one word is read. The FULL flag will remain asserted because a complete word cannot be written at this point.

### Variable Aspect Ratio and Cascading

Variable aspect ratio and cascading allow users to configure the memory in the width and depth required. The memory block can be configured as a FIFO by combining the basic memory block with dedicated FIFO controller logic. The FIFO macro is named FIFO4KX18. Low power flash device RAM can be configured as 1, 2, 4, 9, or 18 bits wide. By cascading the memory blocks, any multiple of those widths can be created. The RAM blocks can be from 256 to 4,096 bits deep, depending on the aspect ratio, and the blocks can also be cascaded to create deeper areas. Refer to the aspect ratios available for each macro cell in the "SRAM Features" section on page 137. The largest continuous configurable memory area is equal to half the total memory available on the device, because the RAM is separated into two groups, one on each side of the device.

The SmartGen core generator will automatically configure and cascade both RAM and FIFO blocks. Cascading is accomplished using dedicated memory logic and does not consume user gates for depths up to 4,096 bits deep and widths up to 18, depending on the configuration. Deeper memory will utilize some user gates to multiplex the outputs.

Generated RAM and FIFO macros can be created as either structural VHDL or Verilog for easy instantiation into the design. Users of Libero SoC can create a symbol for the macro and incorporate it into a design schematic.

Table 6-10 on page 147 shows the number of memory blocks required for each of the supported depth and width memory configurations, and for each depth and width combination. For example, a 256-bit deep by 32-bit wide two-port RAM would consist of two 256×18 RAM blocks. The first 18 bits would be stored in the first RAM block, and the remaining 14 bits would be implemented in the other 256×18 RAM block. This second RAM block would have four bits of unused storage. Similarly, a dual-port memory block that is 8,192 bits deep and 8 bits wide would be implemented using 16 memory blocks. The dual-port memory would be configured in a 4,096×1 aspect ratio. These blocks would then be cascaded two deep to achieve 8,192 bits of depth, and eight wide to achieve the eight bits of width.

# I/O Software Support

In Microsemi's Libero software, default settings have been defined for the various I/O standards supported. Changes can be made to the default settings via the use of attributes; however, not all I/O attributes are applicable for all I/O standards.

Table 7-15 • nano I/O Attributes vs. I/O Standard Applications

	SLEW				LOAD it only)			
I/O Standard	(output only)	OUT_DRIVE (output only)	RES_PULL	IGLOO nano	ProASIC 3 nano	Schmitt Trigger	Hold State	Combine Register
LVTTL/ LVCMOS3.3	1	<b>√</b> (8)	✓	1	1	✓	1	1
LVCMOS2.5	1	<b>√</b> (8)	✓	✓	✓	✓	✓	✓
LVCMOS1.8	1	<b>√</b> (4)	✓	1	✓	✓	✓	✓
LVCMOS1.5	1	<b>√</b> (2)	✓	1	✓	✓	✓	✓
LVCMOS1.2	1	<b>√</b> (2)	✓	1	_	1	✓	✓
Software Defaults	HIGH	Refer to numbers in parentheses in above cells.	None	All Devices: 5 pF	10 pF or 35 pF*	Off	Off	No

Note: \*10 pF for A3PN010, A3PN015, and A3PN020; 35 pF for A3PN060, A3PN125, and A3PN250.





Figure 8-13 • Selecting VREF Voltage for the I/O Bank

# **Assigning VREF Pins for a Bank**

The user can use default pins for VREF. In this case, select the **Use default pins for VREFs** check box (Figure 8-13). This option guarantees full VREF coverage of the bank. The equivalent PDC command is as follows:

```
set_vref_default [bank name]
```

To be able to choose VREF pins, adequate VREF pins must be created to allow legal placement of the compatible voltage-referenced I/Os.

To assign VREF pins manually, the PDC command is as follows:

```
set_vref -bank [bank name] [package pin numbers]
```

For ChipPlanner/PinEditor to show the range of a VREF pin, perform the following steps:

- 1. Assign VCCI to a bank using MVN > Edit > I/O Bank Settings.
- 2. Open **ChipPlanner**. Zoom in on an I/O package pin in that bank.
- 3. Highlight the pin and then right-click. Choose Use Pin for VREF.

Boundary Scan in Low Power Flash Devices

# Microsemi's Flash Devices Support the JTAG Feature

The flash-based FPGAs listed in Table 15-1 support the JTAG feature and the functions described in this document.

#### Table 15-1 • Flash-Based FPGAs

Series	Family*	Description
IGL00	IGL00	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLO0e	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC <sup>®</sup> 3 FPGA fabric, programmable analog block, support for ARM <sup>®</sup> Cortex <sup>™</sup> -M1 soft processors, and flash memory into a monolithic device

Note: \*The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

### IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 15-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

### **ProASIC3 Terminology**

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 15-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.



### **Internal Pull-Up and Pull-Down**

Low power flash device I/Os are equipped with internal weak pull-up/-down resistors that can be used by designers. If used, these internal pull-up/-down resistors will be activated during power-up, once both VCC and VCCI are above their functional activation level. Similarly, during power-down, these internal pull-up/-down resistors will turn off once the first supply voltage falls below its brownout deactivation level.

# **Cold-Sparing**

In cold-sparing applications, voltage can be applied to device I/Os before and during power-up. Cold-sparing applications rely on three important characteristics of the device:

- 1. I/Os must be tristated before and during power-up.
- 2. Voltage applied to the I/Os must not power up any part of the device.
- 3. VCCI should not exceed 3.6 V, per datasheet specifications.

As described in the "Power-Up to Functional Time" section on page 312, Microsemi's low power flash I/Os are tristated before and during power-up until the last voltage supply (VCC or VCCI) is powered up past its functional level. Furthermore, applying voltage to the FPGA I/Os does not pull up VCC or VCCI and, therefore, does not partially power up the device. Table 17-4 includes the cold-sparing test results on A3PE600-PQ208 devices. In this test, leakage current on the device I/O and residual voltage on the power supply rails were measured while voltage was applied to the I/O before power-up.

Table 17-4 • Cold-Sparing Test Results for A3PE600 Devices

	Residual \		
Device I/O	VCC	VCCI	Leakage Current
Input	0	0.003	<1 µA
Output	0	0.003	<1 µA

VCCI must not exceed 3.6 V, as stated in the datasheet specification. Therefore, ProASIC3E devices meet all three requirements stated earlier in this section and are suitable for cold-sparing applications.

The following devices and families support cold-sparing:

- IGLOO: AGL015 and AGL030
- All IGLOO nano
- All IGLOO PLUS
- All IGLOOe
- ProASIC3L: A3PE3000L
- ProASIC3: A3P015 and A3P030
- All ProASIC3 nano
- All ProASIC3E
- Military ProASIC3EL: A3PE600L and A3PE3000L
- RT ProASIC3: RT3PE600L and RT3PE3000L

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